

# -30V, -11A, 16mΩ P-channel Power Trench MOSFET

## JMTP160P03D

### Features

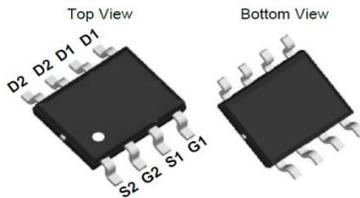
- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS Tested
- Halogen-free; RoHS-compliant
- Pb-free plating

### Applications

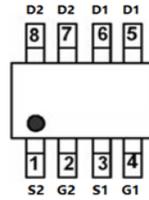
- Load Switch
- PWM Application
- Power Management

### Product Summary

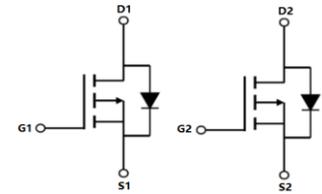
Parameters	Value	Unit
$V_{DSS}$	-30	V
$V_{GS(th\_Typ)}$	-1.7	V
$I_D(@V_{GS}=10V)$	-11	A
$R_{DS(ON\_Typ)}(@V_{GS}=-10V)$	12	mΩ
$R_{DS(ON\_Typ)}(@V_{GS}=-4.5V)$	16	mΩ



SOP-8L\_Dual



Pin Assignment



Schematic Diagram

### Ordering Information

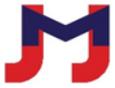
Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTP160P03D	160P03D	3	Tape&Reel	SOP-8	4000	48000

### Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	-30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_A = 25^\circ\text{C}$	-11
		$T_A = 100^\circ\text{C}$	-7
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	65	mJ
$P_D$	Power Dissipation	$T_A = 25^\circ\text{C}$	2.8
		$T_A = 100^\circ\text{C}$	1.1
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	112	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(4)</sup>	45	

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = -250\mu\text{A}$ , $V_{GS} = 0\text{V}$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{V}$ , $V_{GS} = 0\text{V}$	-	-	-1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}$ , $V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = -250\mu\text{A}$	-1.2	-1.7	-2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(5)</sup>	$V_{GS} = -10\text{V}$ , $I_D = -10\text{A}$	-	12	17	$\text{m}\Omega$
		$V_{GS} = -4.5\text{V}$ , $I_D = -5\text{A}$	-	16	27	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	7	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}$ , $V_{DS} = -15\text{V}$ , $f = 1\text{MHz}$	1763	2468	3331	pF
$C_{oss}$	Output Capacitance		184	258	348	pF
$C_{rss}$	Reverse Transfer Capacitance		164	230	310	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0$ to $-10\text{V}$ $V_{DS} = -15\text{V}$ , $I_D = -10\text{A}$	33	46	62	nC
$Q_{gs}$	Gate Source Charge		-	8.2	-	nC
$Q_{gd}$	Gate Drain("Miller") Charge		-	8.1	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = -10\text{V}$ , $V_{DD} = -30\text{V}$ $I_D = -9\text{A}$ , $R_{GEN} = 3\Omega$	-	7	-	ns
$t_r$	Turn-On Rise Time		-	2	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	76	-	ns
$t_f$	Turn-Off Fall Time		-	33	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	-11	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	-44	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}$ , $I_S = -10\text{A}$	-		-1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = -10\text{A}$ , $di/dt = 100\text{A}/\mu\text{s}$	10	14	19	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	5.3	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = -15\text{V}$ ,  $V_{GS} = -10\text{V}$ ,  $R_G = 25\text{ohm}$ ,  $L = 0.5\text{mH}$ ,  $I_{AS} = -16.1\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a minimum recommended pad of 2oz copper FR4 PCB.
  4.  $R_{\theta JA}$  is measured with the device mounted on a 1inch<sup>2</sup> pad of 2oz copper FR4 PCB.
  5. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .



## Typical Performance Characteristics

Figure 1: Power De-rating

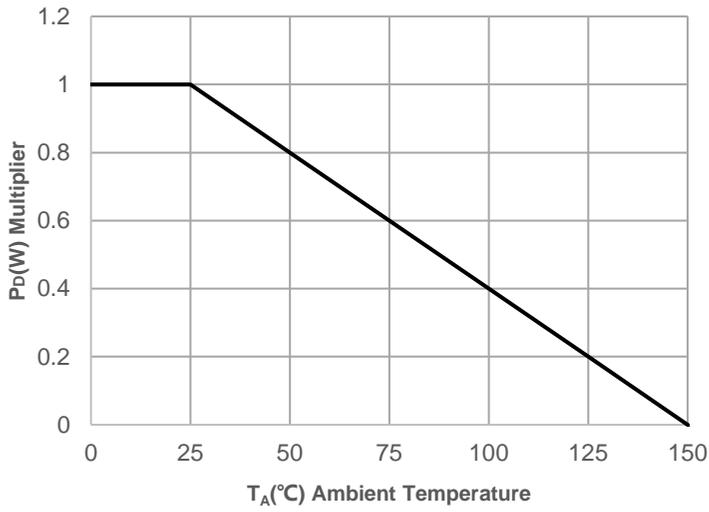


Figure 2: Current De-rating

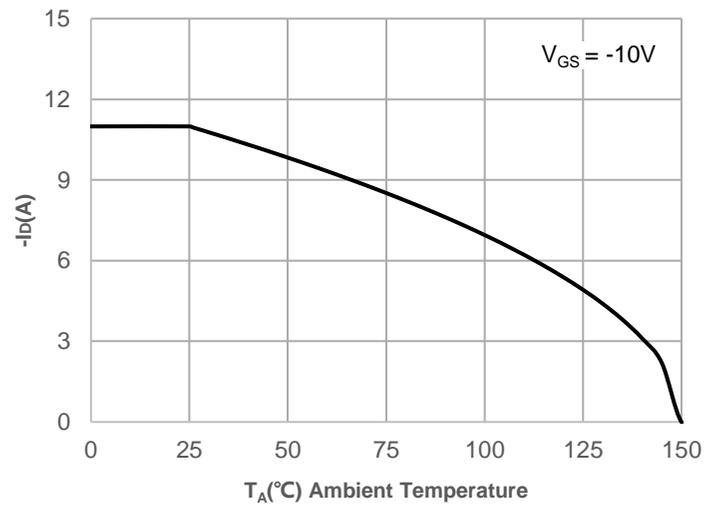


Figure 3: Normalized Maximum Transient Thermal Impedance

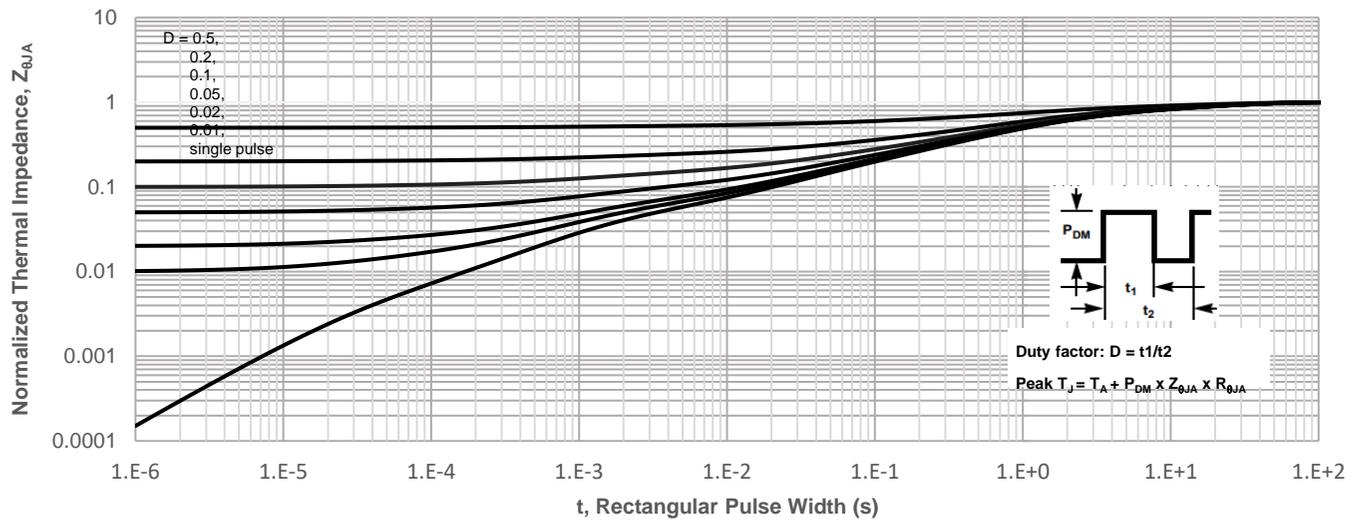
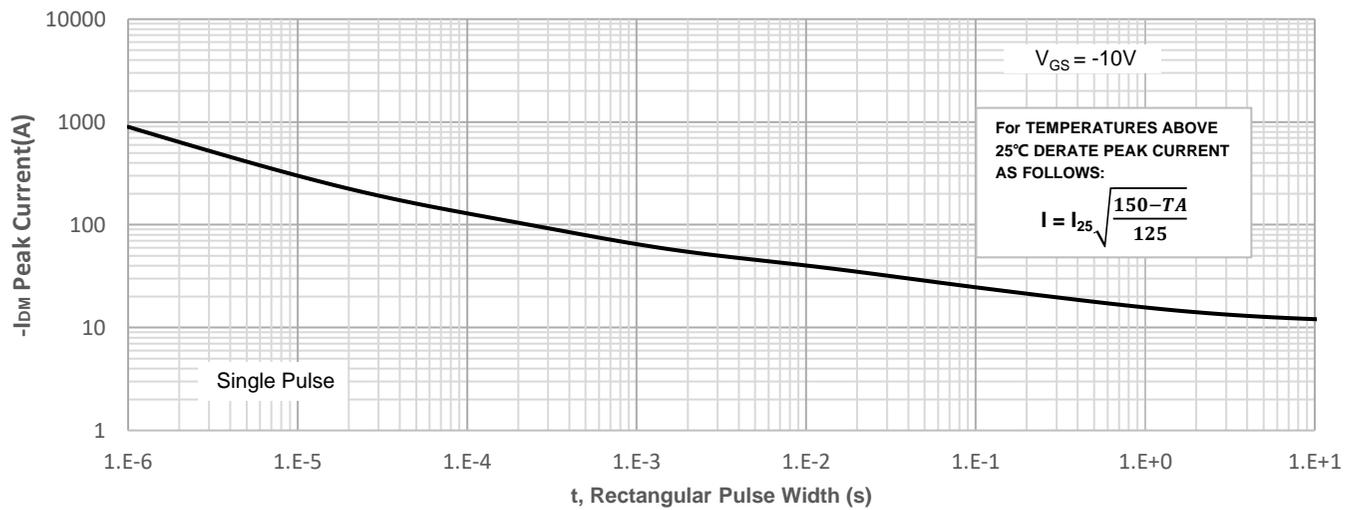


Figure 4: Peak Current Capacity



## Typical Performance Characteristics

Figure 5: Output Characteristics

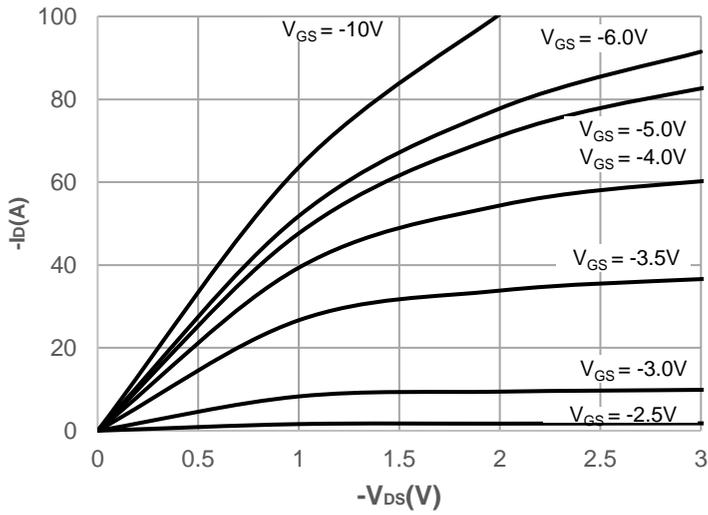


Figure 6: Typical Transfer Characteristics

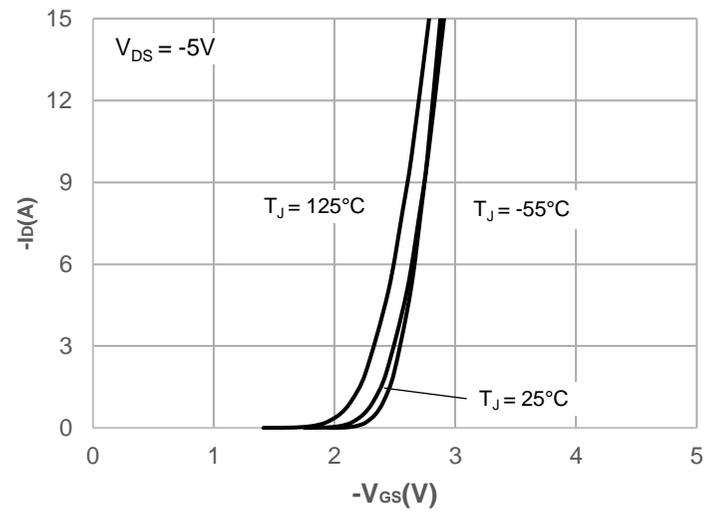


Figure 7: On-resistance vs. Drain Current

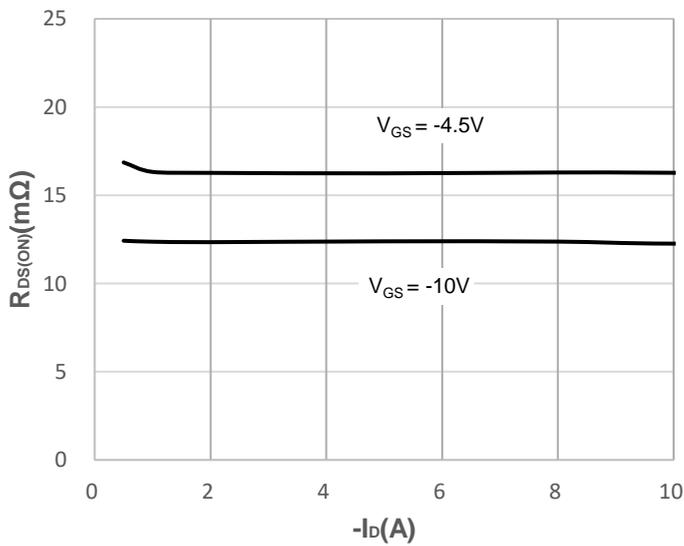


Figure 8: Body Diode Characteristics

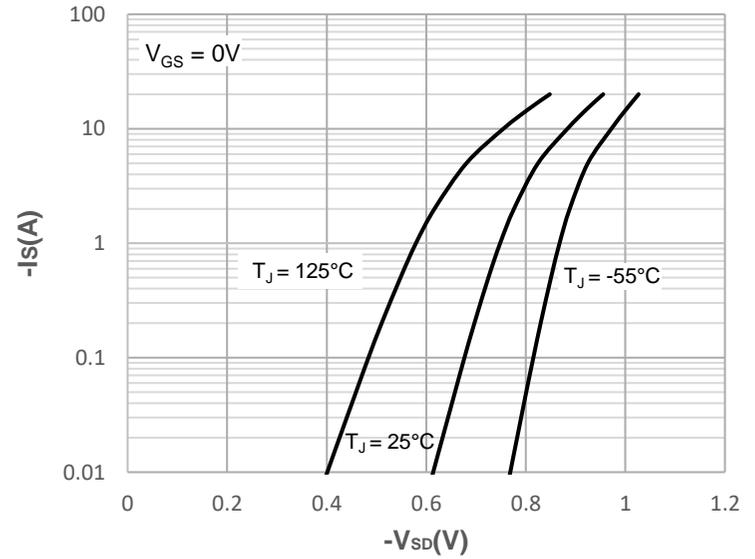


Figure 9: Gate Charge Characteristics

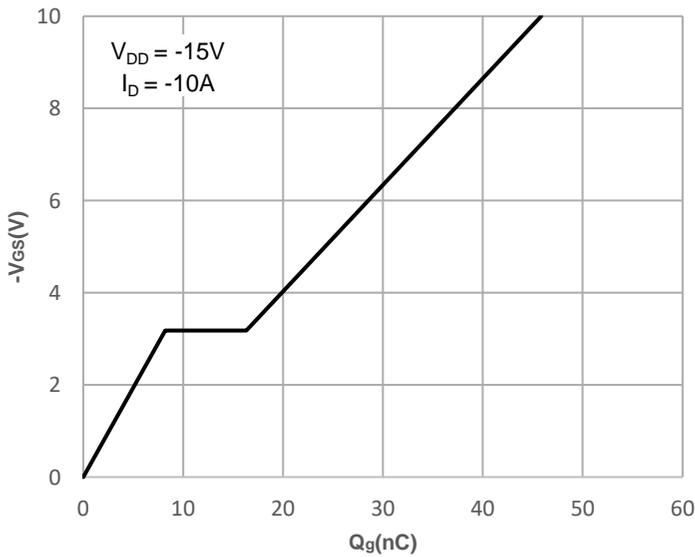
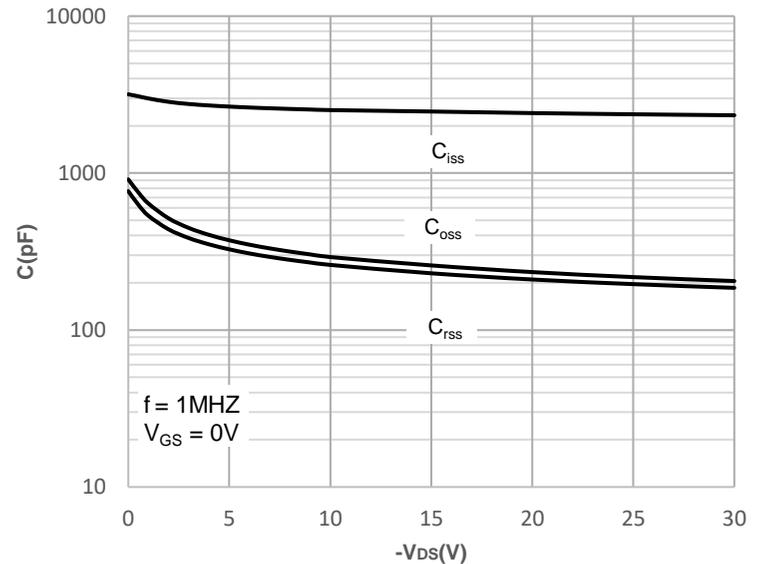
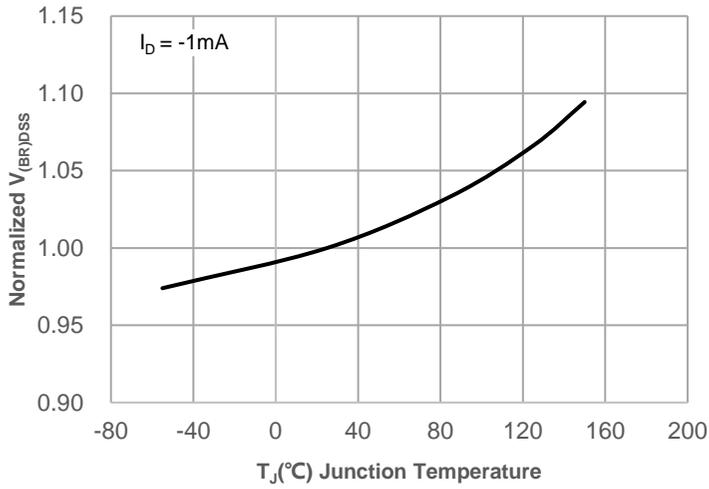


Figure 10: Capacitance Characteristics

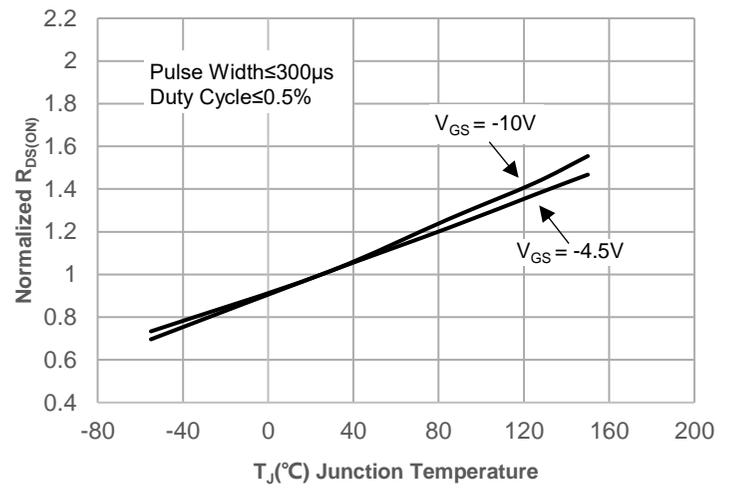


## Typical Performance Characteristics

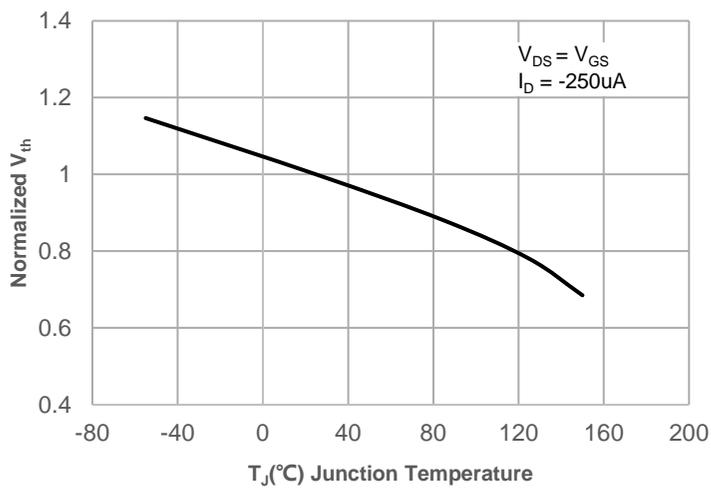
**Figure 11: Normalized Breakdown voltage vs. Junction Temperature**



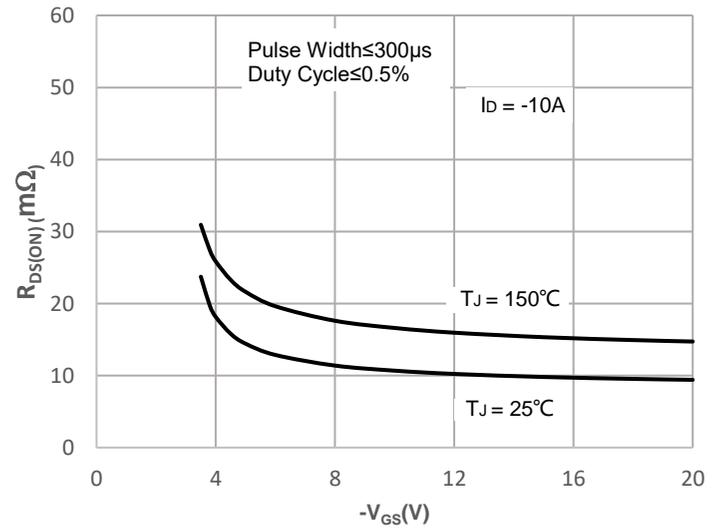
**Figure 12: Normalized on Resistance vs. Junction Temperature**



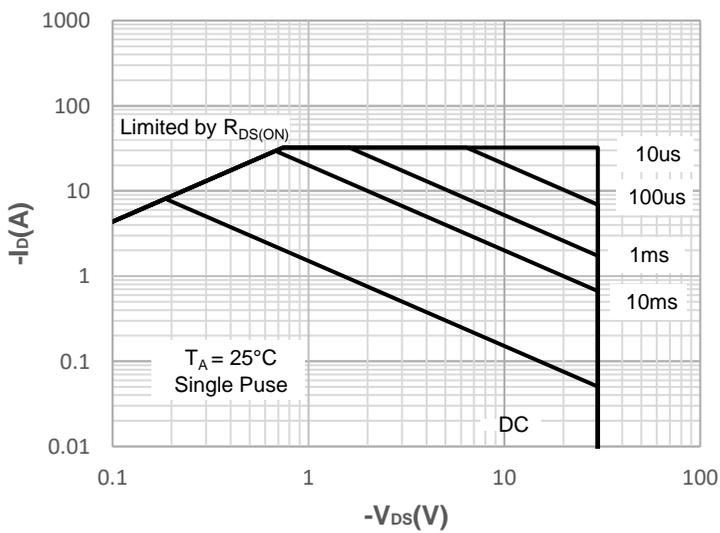
**Figure 13: Normalized Threshold Voltage vs. Junction Temperature**



**Figure 14:  $R_{DS(ON)}$  vs.  $V_{GS}$**



**Figure 15: Maximum Safe Operating Area**



Test Circuit

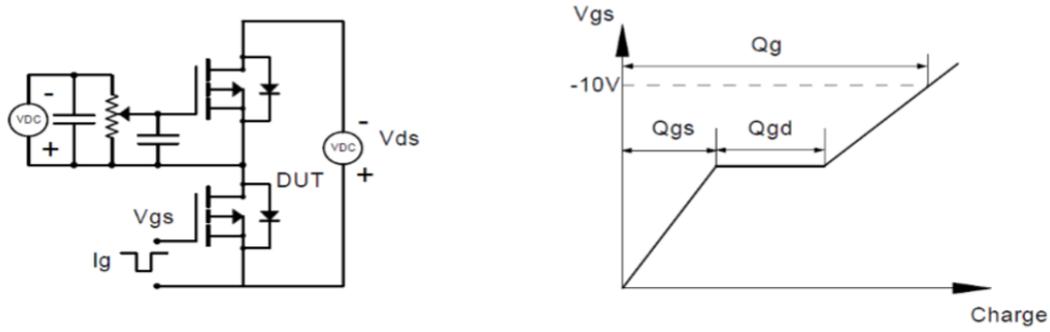


Figure 1: Gate Charge Test Circuit & Waveform

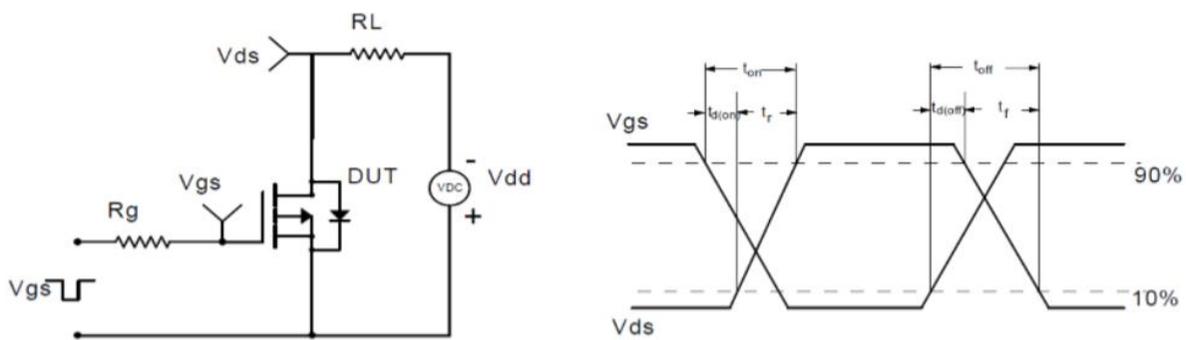


Figure 2: Resistive Switching Test Circuit & Waveform

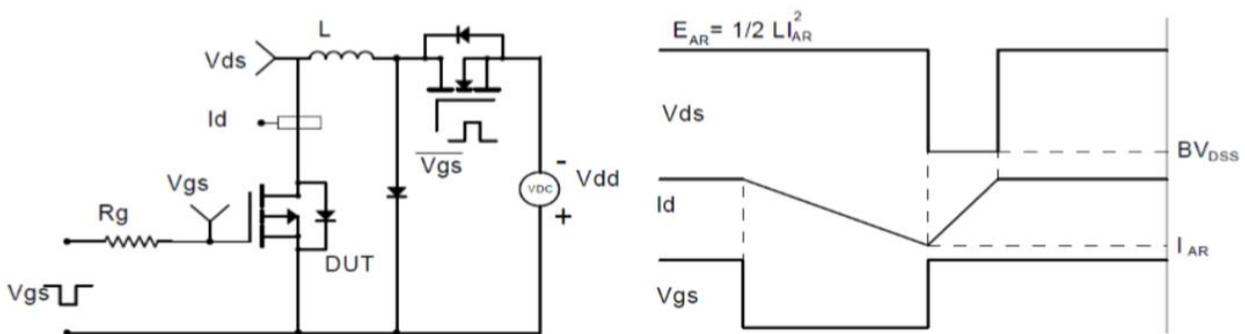


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

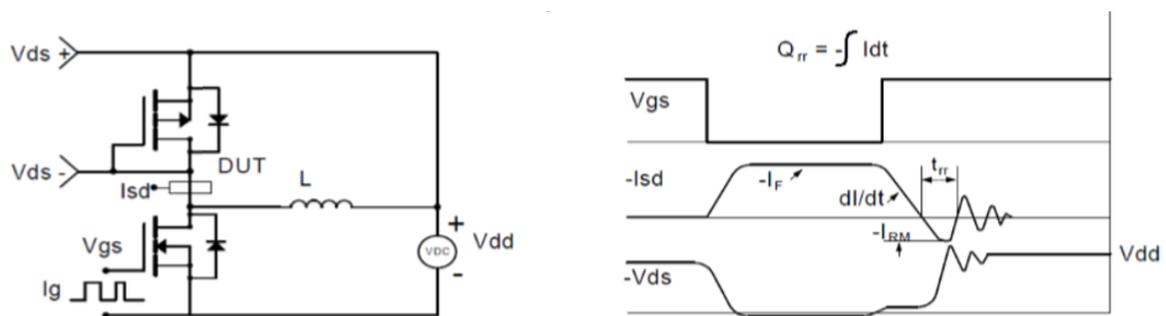
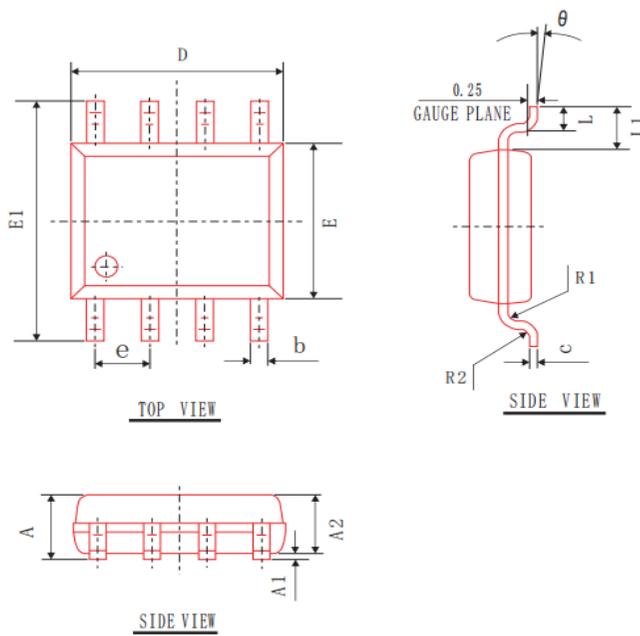
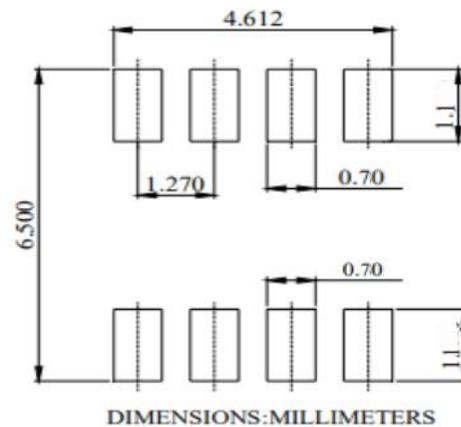


Figure 4: Diode Recovery Test Circuit & Waveform



**Package Mechanical Data(SOP-8L)**

 COMMON DIMENSIONS  
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
$\theta$	2°	4°	6°
L 1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		

**Recommended Footprint**


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